

**2SA1502,
2SC3863**



2018A

PNP/NPN Epitaxial Planar
Silicon Transistors

Switching Applications

(with Bias Resistances $R1=2.2k\Omega$, $R2=10k\Omega$)

©2108A

Applications

- Switching circuits, inverter circuits, interface circuits, driver circuits

Features

- On-chip bias resistance: $R1=2.2k\Omega$, $R2=10k\Omega$
- Small-sized package: CP

(): 2SA1502.

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

| | | | unit |
|------------------------------|------------|-------------|------------------|
| Collector to Base Voltage | V_{CB0} | (-)50 | V |
| Collector to Emitter Voltage | V_{CEO} | (-)50 | V |
| Emitter to Base Voltage | V_{EBO} | (-)6 | V |
| Collector Current | I_C | (-)100 | mA |
| Peak Collector Current | i_C | (-)200 | mA |
| Collector Dissipation | P_C^{cp} | 200 | mW |
| Junction Temperature | T_J | 150 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

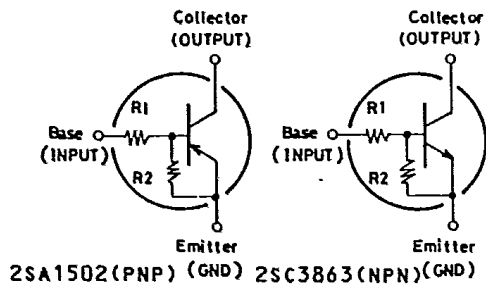
Electrical Characteristics at $T_a=25^\circ\text{C}$

| | | | min | typ | max | unit |
|---|---------------|---|--------|--------|--------|---------------|
| Collector Cutoff Current | I_{CBO} | $V_{CB}=(-)40\text{V}, I_E=0$ | | | (-)0.1 | μA |
| Collector Cutoff Current | I_{CEO} | $V_{CE}=(-)40\text{V}, I_B=0$ | | | (-)0.5 | μA |
| Emitter Cutoff Current | I_{ERO} | $V_{EB}=(-)5\text{V}, I_C=0$ | (-)315 | (-)410 | (-)590 | μA |
| DC Current Gain | h_{FE} | $V_{CE}=(-)5\text{V}, I_C=(-)10\text{mA}$ | 50 | | | |
| Gain-Bandwidth Product | f_T | $V_{CE}=(-)10\text{V}, I_C=(-)5\text{mA}$ | | 250 | | MHz |
| | | | | (200) | | MHz |
| Output Capacitance | c_{ob} | $V_{CB}=(-)10\text{V}, f=1\text{MHz}$ | | 3.5 | | pF |
| | | | | (5.3) | | pF |
| Collector to Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C=(-)10\text{mA}, I_B=(-)0.5\text{mA}$ | | (-)0.1 | (-)0.3 | V |

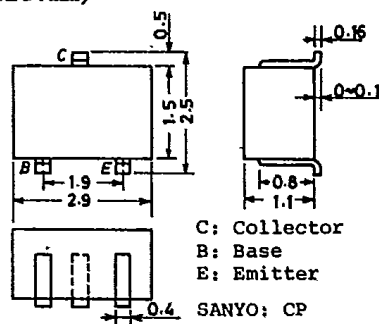
Marking: 2SA1502: HL, 2SC3863: QY

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Electrical Connection



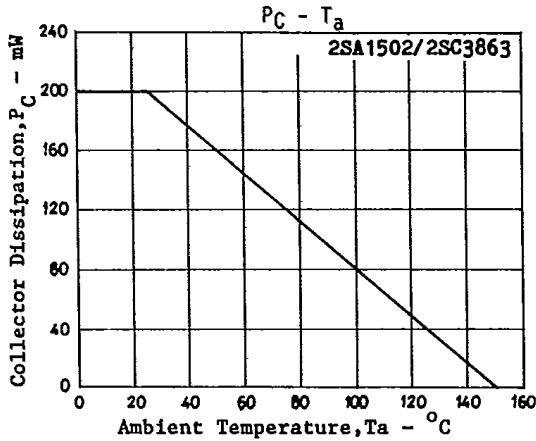
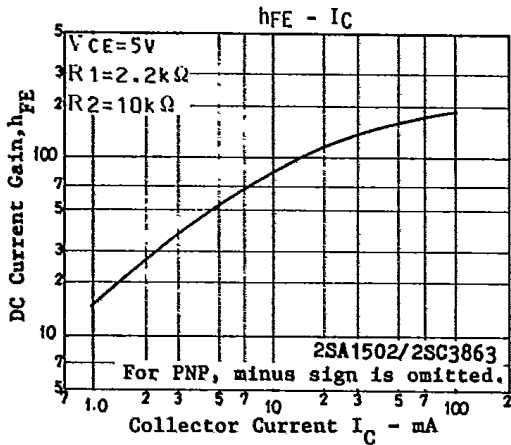
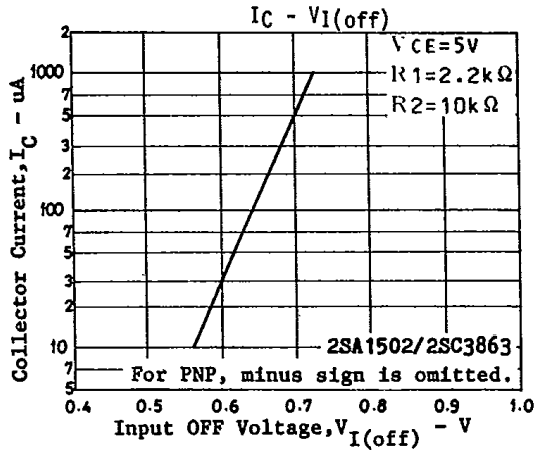
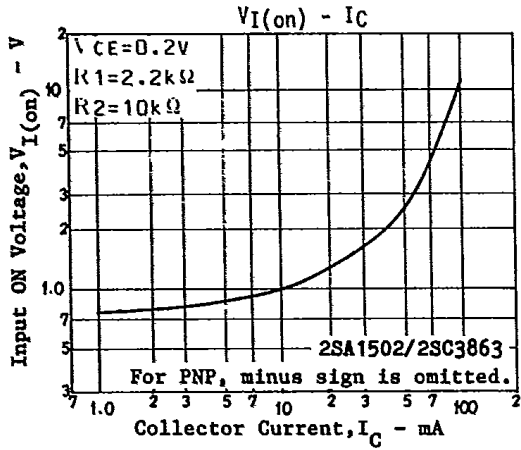
Case Outline 2018A (unit:mm)



2SA1502/2SC3863

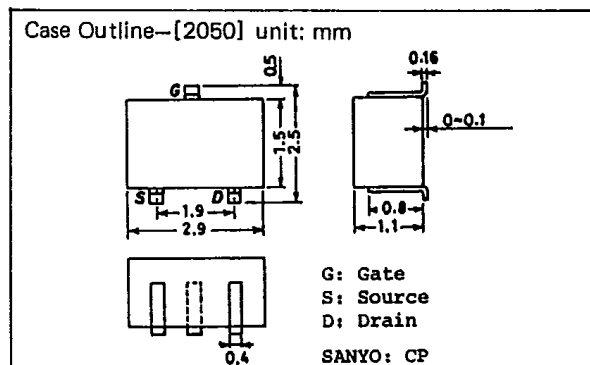
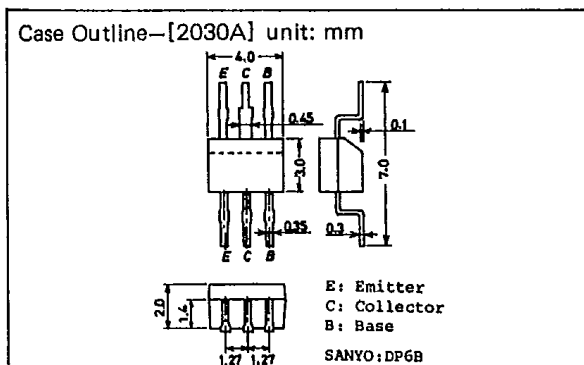
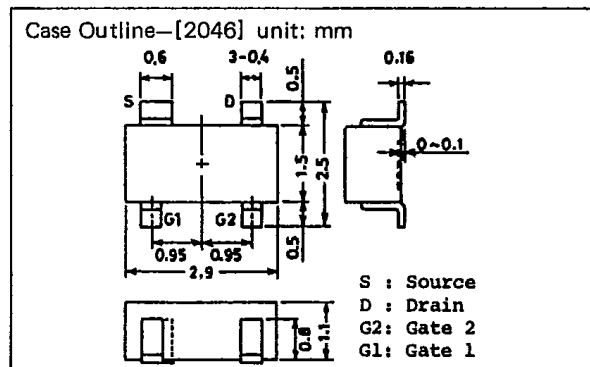
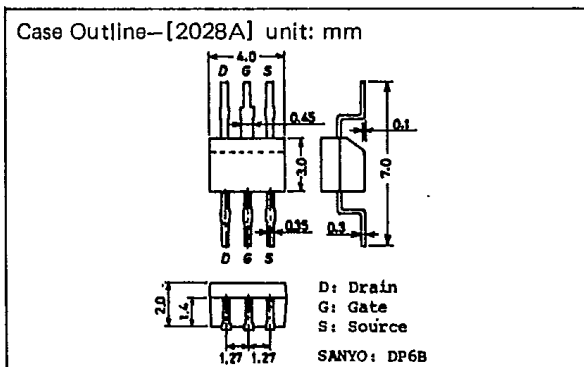
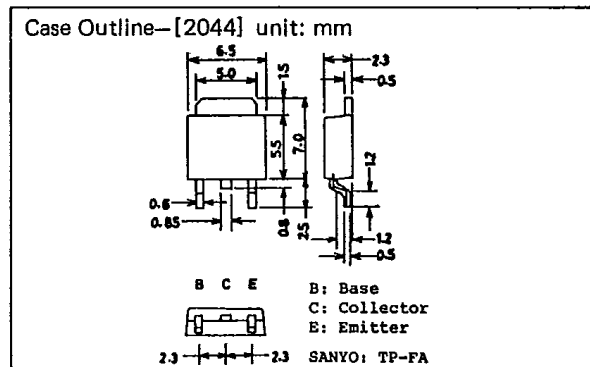
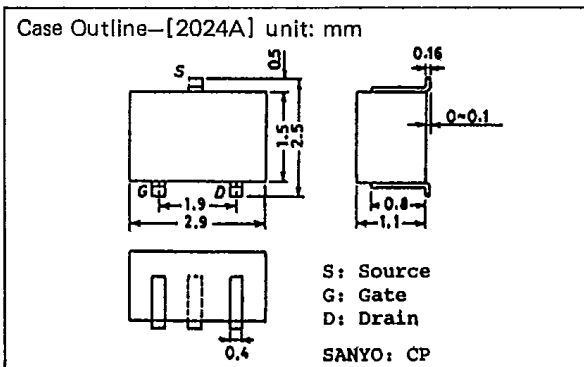
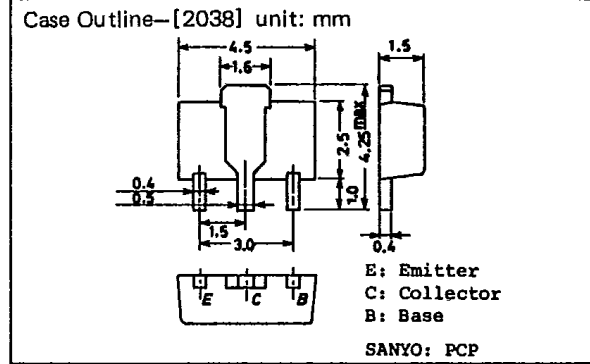
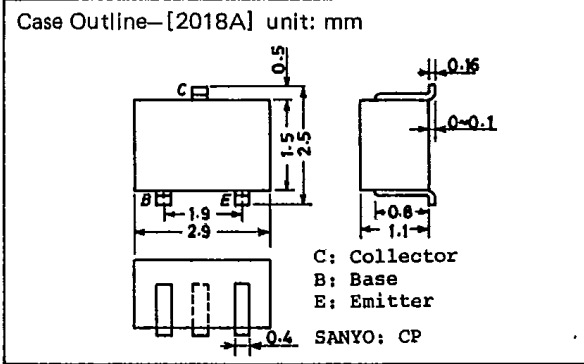
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| | | | min | typ | max | unit |
|--|---------------|----------------------------------|--------|--------|--------|------|
| Collector to Base Breakdown Voltage | $V_{(BR)CBO}$ | $I_C=(-)10\mu A, I_E=0$ | (-)50 | | | V |
| Collector to Emitter Breakdown Voltage | $V_{(BR)CEO}$ | $I_C=(-)100\mu A, R_{BE}=\infty$ | (-)50 | | | V |
| Input OFF Voltage | $V_{I(off)}$ | $V_{CE}=(-)5V, I_C=100\mu A$ | (-)0.5 | (-)0.7 | (-)0.9 | V |
| Input ON Voltage | $V_{I(on)}$ | $V_{CE}=(-)0.2V, I_C=(-)10mA$ | (-)0.7 | (-)1.0 | (-)1.8 | V |
| Input Resistance | R_I | | 1.5 | 2.2 | 2.9 | kohm |
| Resistance Ratio | R_1/R_2 | | 0.198 | 0.22 | 0.242 | |

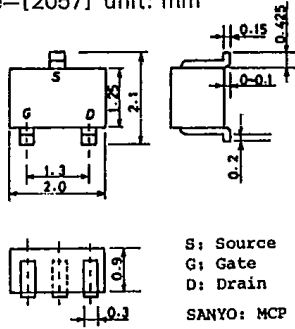


CASE OUTLINES OF SURFACE MOUNT TRANSISTORS

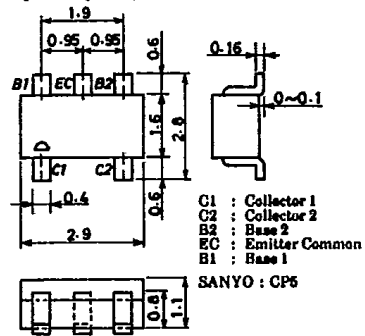
- All of Sanyo surface mount transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.



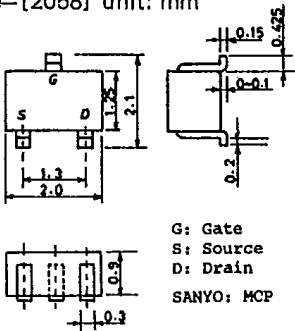
Case Outline—[2057] unit: mm



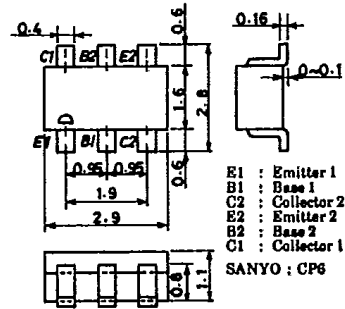
Case Outline—[2066] unit: mm



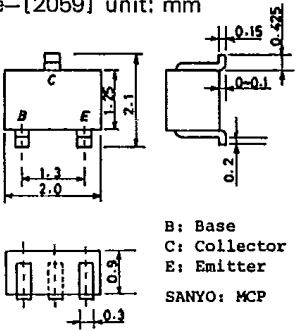
Case Outline—[2058] unit: mm



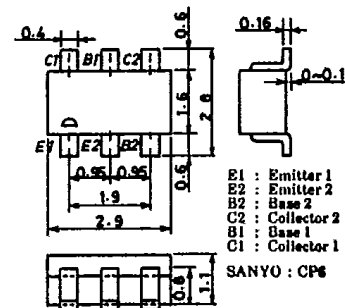
Case Outline—[2067] unit: mm



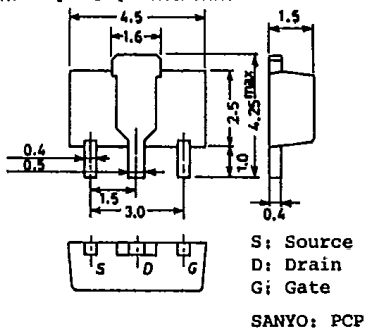
Case Outline—[2059] unit: mm



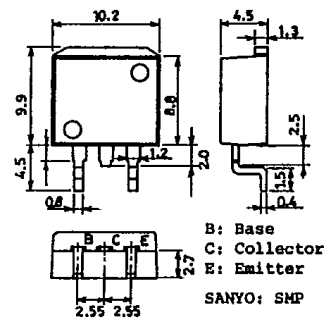
Case Outline—[2068] unit: mm



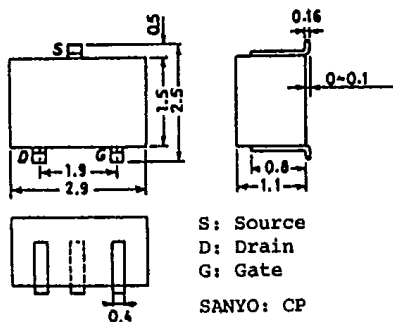
Case Outline—[2062] unit: mm



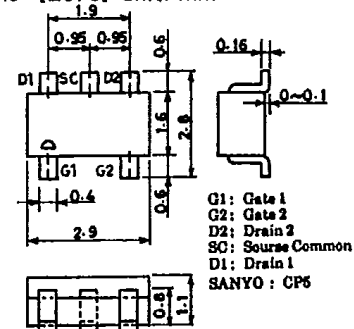
Case Outline—[2069] unit: mm



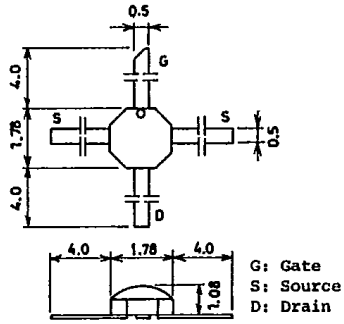
Case Outline—[2065] unit: mm



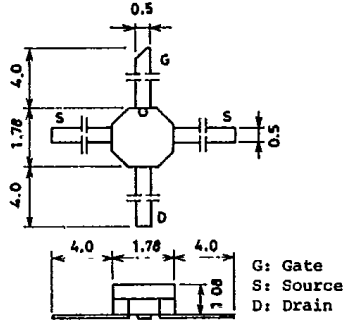
Case Outline—[2070] unit: mm



Case Outline—[2071] unit: mm



Case Outline—[2072] unit: mm



Case Outline—[2073] unit: mm

